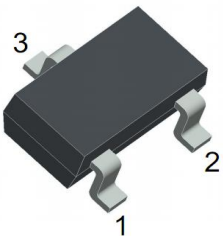
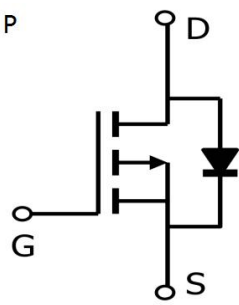
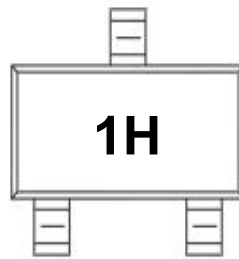
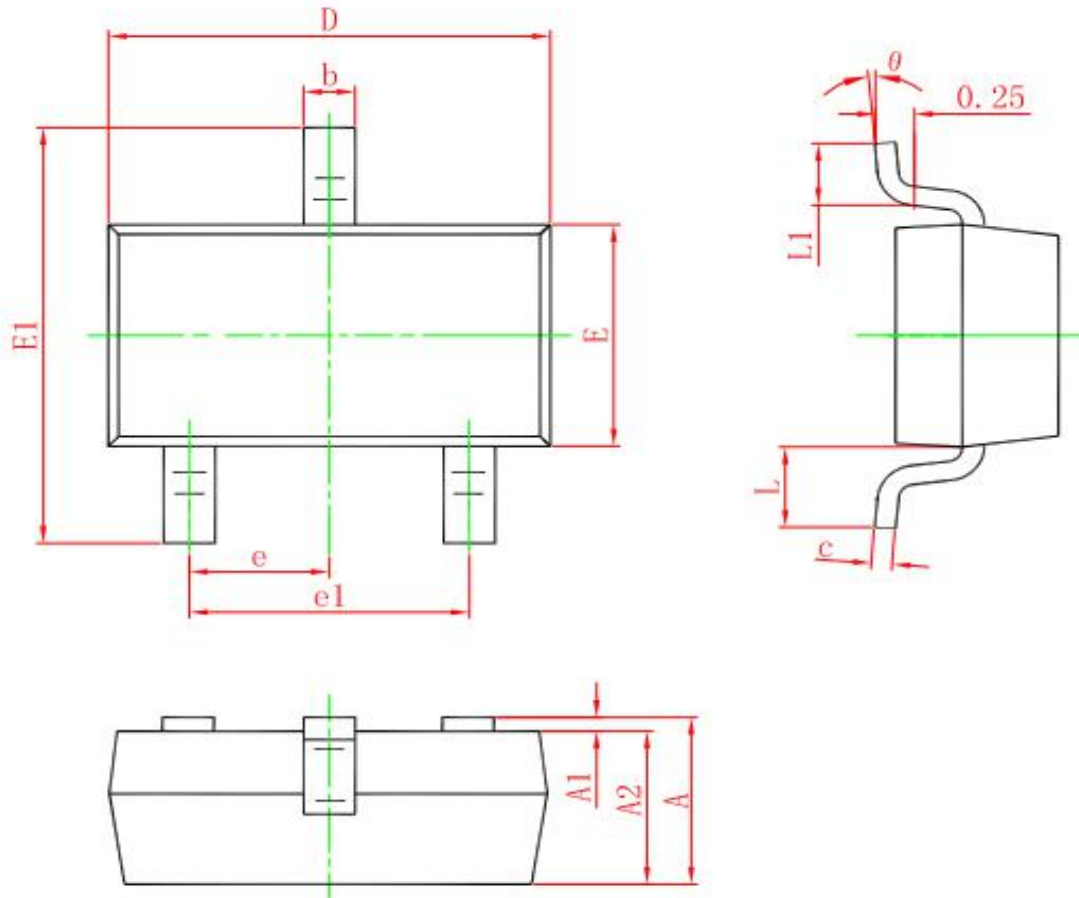


P-Channel 30-V(D-S) MOSFET		SOT-23 Plastic-Encapsulate MOSFETS	
<p style="text-align: center;"><u>SOT-23</u></p>  <p>1.GATE 2.SOURCE 3.DRAIN</p> <p style="text-align: center;">Equivalent Circuit</p> 		<p>Features</p> <ul style="list-style-type: none"> • TrenchFET Power MOSFET • Ultra Low On-Resistance • Available in Tape and Reel <p>Application</p> <ul style="list-style-type: none"> ※ Load Switch for Portable Devices ※ DC/DC Converter <p>MARKING</p> 	
V(BR)DSS	RDS(on)MAX		ID
-30 V	98mΩ@-10V		-3.0A
	165mΩ@-4.5V		
Maximum ratings (Ta=25°C unless otherwise noted)			
Parameter	Symbol	Value	Unit
Drain-Source Voltage	VDS	-30	V
Gate-Source Voltage	VGS	±20	
Continuous Drain Current	ID	-3.0	A
Pulsed Diode Current	IDM	-24	
Power Dissipation	PD	1.25	W
Thermal Resistance from Junction to Ambient (t≤5s)	RθJA	100	°C/W
Operating Junction	TJ	150	°C
Storage Temperature	TSTG	-55~+150	

MOSFET ELECTRICAL CHARACTERISTICS						
Static Electrical Characteristics (Ta = 25 °C Unless Otherwise Noted)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-source breakdown voltage	V(BR)DSS	VGS = 0V, ID = -250µA	-30			V
Gate-source threshold voltage	VGS(th)	VDS =VGS, ID = -250µA	-1		-2.5	V
Gate-source leakage	IGSS	VDS =0V, VGS = ±20V			±100	nA
Zero gate voltage drain current	IDSS	VDS = -24V, VGS =0V			-1	µA
Drain-source on-state resistancea	RDS(on)	VGS = -10V, ID = -3.0A			98	mΩ
		VGS = -4.5V, ID = -2.5A			165	mΩ
Forward transconductancea	gfs	VDS = -10V, ID = -3A	3.1			S
Diode forward voltage	VSD	IS=-1A, VGS=0V		-0.8	-1.2	V
Continuous Source-Drain Diode Current	IS				-1.3	A
Dynamic						
Input capacitance	Ciss	VDS = -15V, VGS =0V, f=1MHz		510		pF
Output capacitance	Coss			71		pF
Reverse transfer capacitanceb	Crss			43		pF
Total gate charge	Qg	VDS = -15V, VGS = -10V, ID = -3A		9.5		nC
Gate-source charge	Qgs			2.3		nC
Gate-drain charge	Qgd			1.6		nC
Gate resistance	Rg	f=1MHz		6.5		Ω
Switchingb						
Turn-on delay time	td(on)	VDS= -15V RL=6Ω, ID ≈ -1A, VGEN= -10V, Rg=3Ω		12		ns
Rise time	tr			18		ns
Turn-off delay time	td(off)			88		ns
Fall time	tf			52		ns
Body Diode Reverse Recovery Time	Trr	IF= -3.0A, dI/dt=100A/µs		17		ns
Body Diode Reverse Recovery Charge	Qrr	IF= -3.0A, dI/dt=100A/µs		12		nC
Note :						
1. Repetitive Rating : Pulse width limited by maximum junction temperature.						
2. Surface Mounted on FR4 Board, t < 5 sec.						
3. Pulse Test : Pulse Width≤300µs, Duty Cycle ≤ 2%.						
4. Guaranteed by design, not subject to production testing.						

SOT-23 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)